TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (π -MOSV)

TPC8012-H

Switching Regulator Applications DC/DC Converter Applications

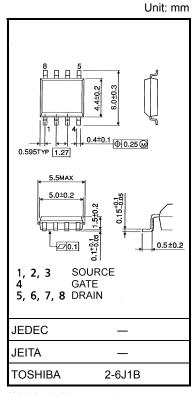
- Low drain-source ON-resistance: RDS (ON) = 0.28Ω (typ.)
- High forward transfer admittance: $|Y_{fs}| = 1.35 S$ (typ.)
- Low leakage current: $IDSS = 100 \mu A (max) (VDS = 200 V)$
- Enhancement mode: $V_{th} = 3.0 \text{ to } 5.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$

Maximum Ratings (Ta = 25°C)

Characte	ristics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	200	V	
Drain-gate voltage (F	$k_{GS} = 20 \text{ k}\Omega$)	V_{DGR}	200	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	I _D	1.8	Α	
Diam current	Pulse (Note 1)	I_{DP}	7.2	ζ	
Drain power dissipati	on $(t = 10 \text{ s})$ (Note 2a)	P_{D}	1.9	W	
Drain power dissipati	on (t = 10 s) (Note 2b)	P_{D}	1.0	W	
Single-pulse avalance	he energy (Note 3)	E _{AS}	2.05	mJ	
Avalanche current		I _{AR}	1.8	Α	
Repetitive avalanche	energy Note 2a) (Note 4)	E _{AR}	0.19	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

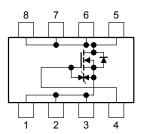
Note: For Notes 1 to 4, refer to the next page.

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.085 g (typ.)

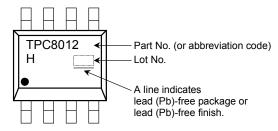
Circuit Configuration



Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R _{th (ch-a)}	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	125	°C/W

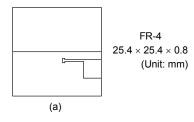
Marking (Note 5)

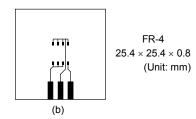


Note 1: The channel temperature should not exceed 150°C during use.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)



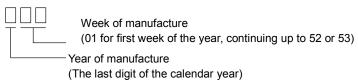


Note 3: $V_{DD} = 50 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 1.0 mH, $R_G = 25 \Omega$, $I_{AR} = 1.8 \text{ A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: • on the lower left of the marking indicates Pin 1.

* Weekly code: (Three digits)



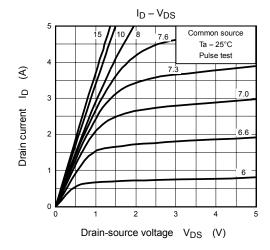
Electrical Characteristics (Ta = 25°C)

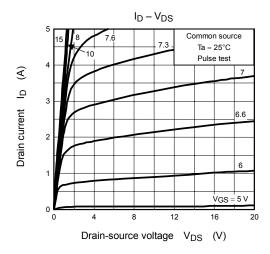
Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GSS}	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	_		±10	μΑ
Drain cutoff curre	ent	I _{DSS}	V _{DS} = 200 V, V _{GS} = 0 V	_		100	μА
Drain-source bre	akdown voltage	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	200	_	_	V
Gate threshold vo	oltage	V _{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	3.0	_	5.0	V
Drain-source ON	-resistance	R _{DS (ON)}	$V_{GS} = 10 \text{ V}, I_D = 0.9 \text{ A}$	_	0.28	0.40	Ω
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 0.9 A	0.65	1.35	_	S
Input capacitance	9	C _{iss}		_	440	_	
Forward transfer admittance Input capacitance Reverse transfer capacitance Output capacitance Rise time Turn-on time		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	80	_	pF
· ·		C _{oss}		_	260	_	
	Rise time	t _r	10 V □ lp = 0.9 A	_	23	_	
Switching time	Turn-on time	t _{on}	$V_{GS} = 0.9 A$ $V_{GS} = 0.9 A$ $V_{OUT} = 0.9 A$	_	28	_	nc
Switching time	Fall time	t _f	R = 11	_	22		ns
	Turn-off time	t _{off}	$V_{DD} \stackrel{\sim}{\simeq} 100 \text{ V}$ Duty \leq 1%, $t_W = 10 \mu\text{s}$	_	73	_	
Total gate charge (gate-source plus							
Gate-source charge 1		Q _{gs}	I _D = 1.8 A	_	6	_	nC
Gate-drain ("Mille	Gate-drain ("Miller") charge			_	5	_	

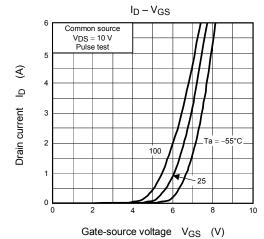
Source-Drain Ratings and Characteristics (Ta = 25°C)

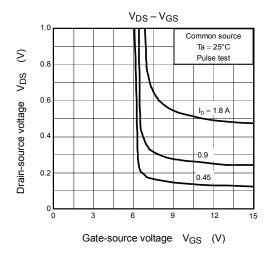
Character	istic		Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse	(Note 1)	I _{DRP}	_	_	_	7.2	Α
Forward voltage (diode)			V_{DSF}	$I_{DR} = 1.8 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	-1.5	V

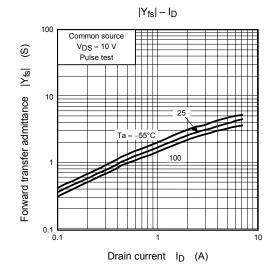
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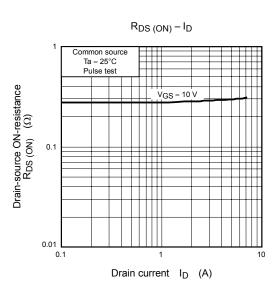




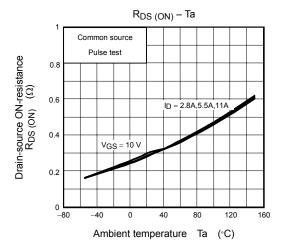


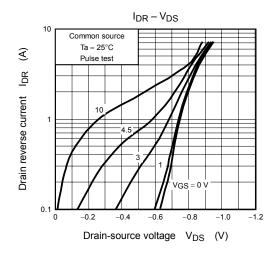


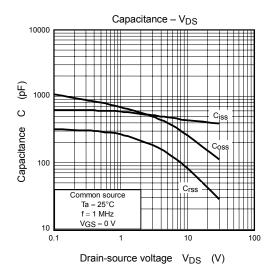


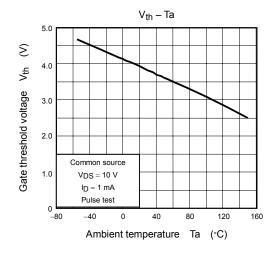


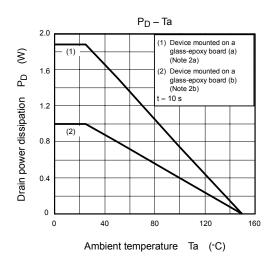
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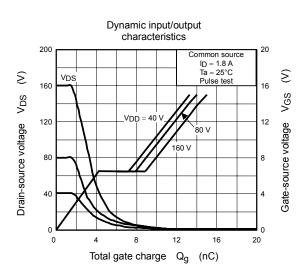


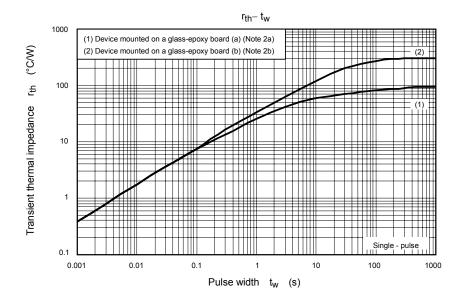


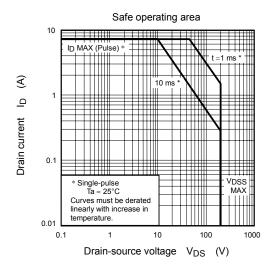












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Handbook" etc. 021023_A

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